

TIP31, TIP32



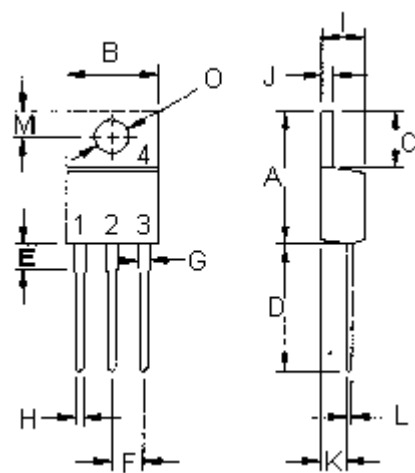
High Power Bipolar Transistors



Features:

- Collector - emitter sustaining voltage - $V_{CEO(sus)}$
= 60 V (Minimum) - TIP31A, TIP32A
= 100 V (Minimum) - TIP31C, TIP32C
- Collector - emitter sustaining voltage - $V_{CE(sat)} = 1.2$ V (Maximum) at $I_C = 3$ A
- Current gain - bandwidth product $f_T = 3$ MHz (Minimum) at $I_C = 500$ mA

TO-220



- Pin**
1. Base
 2. Collector
 3. Emitter
 4. Collector (Case)

Dimensions	Minimum	Maximum
A	14.68	15.31
B	9.78	10.42
C	5.01	6.52
D	13.06	14.62
E	3.57	4.07
F	2.42	3.66
G	1.12	1.36
H	0.72	0.96
I	4.22	4.98
J	1.14	1.38
K	2.2	2.97
L	0.33	0.55
M	2.48	2.98
O	3.7	3.9

Dimensions : Millimetres

NPN
TIP31A
TIP32C

PNP
TIP32A
TIP32C

3 Amperes
Complementary Silicon
Power Transistors
60 - 100 Volts
40 Watts

Maximum Ratings

Characteristic	Symbol	TIP31A TIP32A	TIP31C TIP32C	Unit
Collector - emitter voltage	V _{CEO}	60	100	V
Collector - base voltage	V _{CBO}			
Emitter - base voltage	V _{EBO}	5		A
Collector current - continuous	I _C	3		
- peak		5		
Base current	I _B	1		
Total power dissipation at tc = 25°C derate above 25°C	P _D	40 0.32		W W/°C
Operating and storage junction temperature range	T _J , T _{STG}	-65 to +150		°C

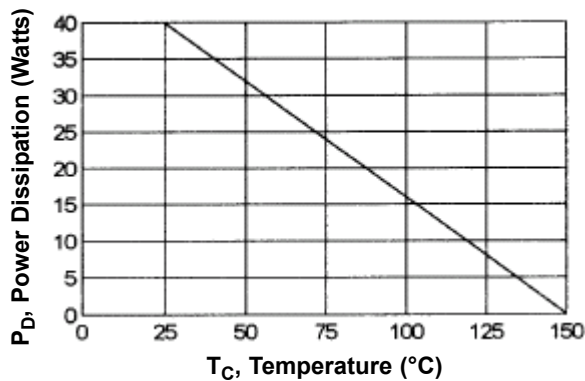
Thermal Characteristics

Characteristic	Symbol	Maximum	Unit
Thermal resistance junction to case	$R_{\theta jc}$	3.125	$^\circ\text{C/W}$

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Figure - 1 Power Derating



Electrical Characteristics ($T_C = 25^\circ\text{C}$ Unless Otherwise Noted)

Characteristic	Symbol	Minimum	Maximum	Unit
OFF Characteristics				
Collector - emitter sustaining voltage (1) (I _C = 30 mA, I _B = 0) TIP31A, TIP32A TIP31C, TIP32C	V _{CEO (SUS)}	60 100	-	V
Collector cut off current (V _{CE} = 30V, I _B = 0) (V _{CE} = 60V, I _B = 0) TIP31A, TIP32A TIP31C, TIP32C	I _{CEO}	-	0.3	mA
Collector cut off current (V _{CE} = 60 V, V _{EB} = 0) (V _{CE} = 100 V, V _{EB} = 0) TIP31A, TIP32A TIP31C, TIP32C	I _{CES}	-	0.2	
Emitter cut off current (V _{EB} = 5 V, I _C = 0)	I _{EBO}	-	1	
ON Characteristics (1)				
DC current gain (I _C = 1 A, V _{CE} = 4 V) (I _C = 3 A, V _{CE} = 4 V)	h _{FE}	25 15	- 50	-
Collector - emitter saturation voltage (I _C = 3 A, I _B = 375 mA)	V _{CE (sat)}	-	1.2	V
Base - emitter on voltage (I _C = 3 A, V _{CE} = 4 V)	V _{BE (on)}	-	1.8	
Dynamic Characteristics				
Current gain - bandwidth product (2) (I _C = 500 mA, V _{CE} = 10 V, f _{TEST} = 1 KHz)	f _T	3	-	MHz
Small - signal current gain (I _C = 500 A, V _{CE} = 10 V, f = 1 kHz)	h _{fe}	20	-	-

(1) Pulse Test : Pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$

(2) $f_T = |h_{FE}| \cdot f_{TEST}$

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Figure - 2 Switching Time Equivalent Circuit

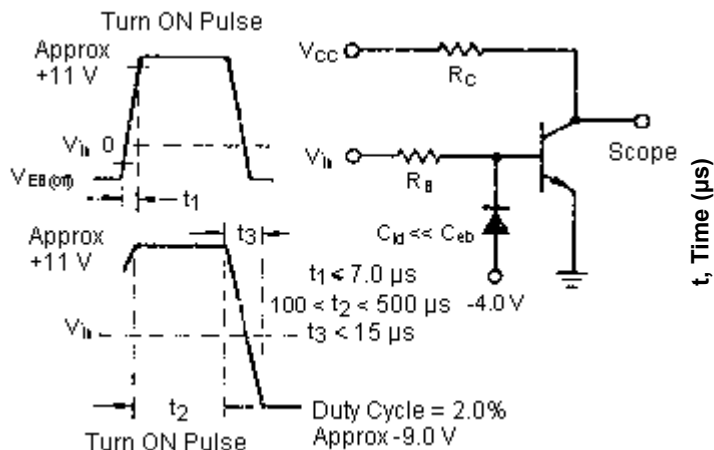


Figure - 3 Turn-On Time

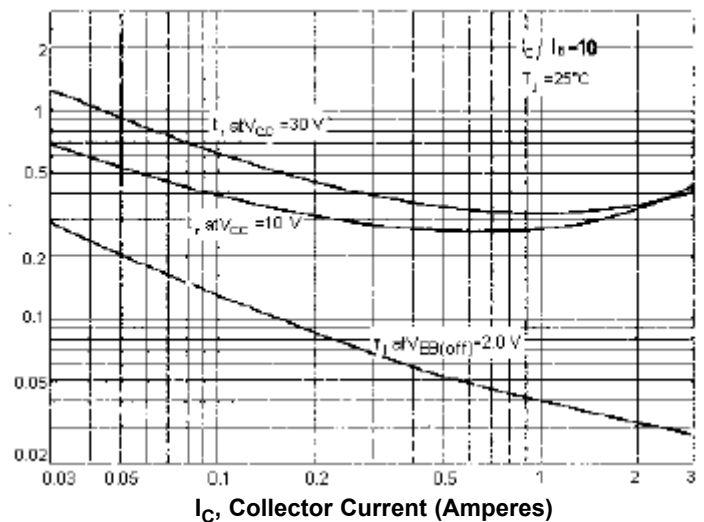


Figure - 4 DC Current Gain

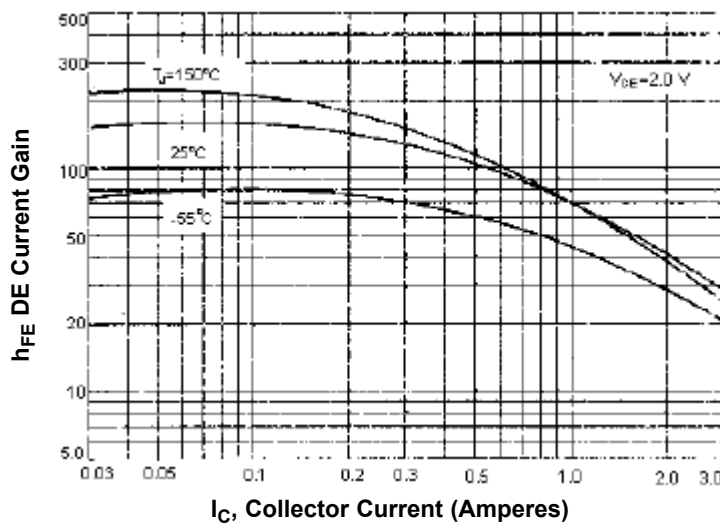


Figure - 5 Turn-Off Time

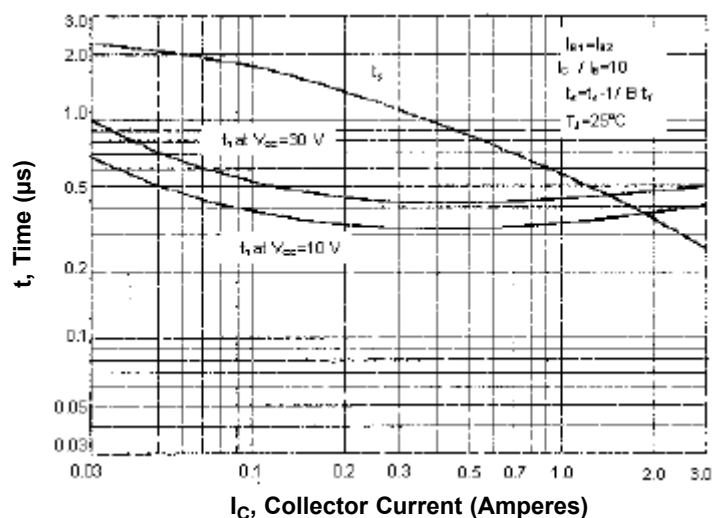
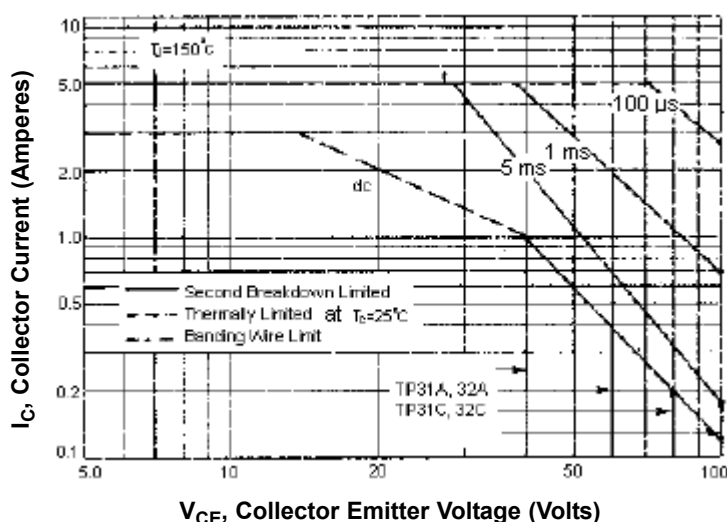


Figure - 6 Active Region Safe Operating Area



There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure - 6 curve is based on $T_J (PK) = 150^\circ C$; T_C is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_J (PK) = 150^\circ C$. At high case temperatures, thermal limitation will reduce the power that can be handled to values less than the limitations imposed by second breakdown

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Figure - 7 Collector Saturation Region

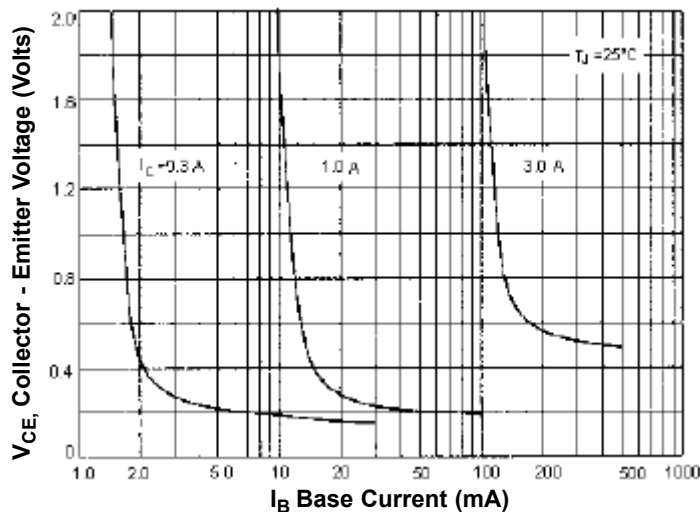


Figure - 8 Capacitances

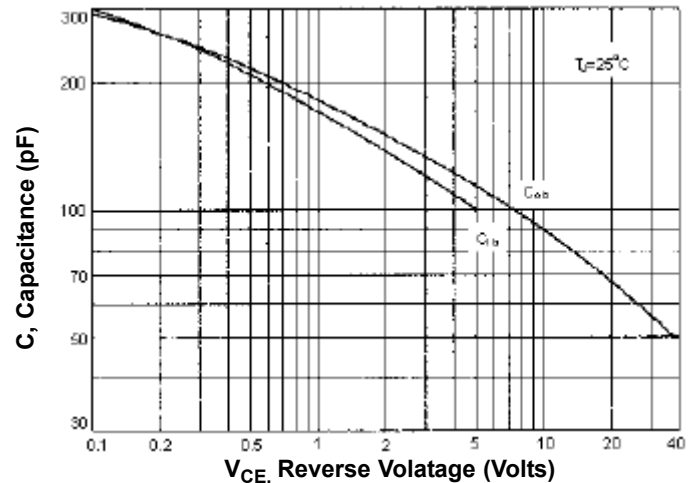


Figure - 9 "ON" Voltage

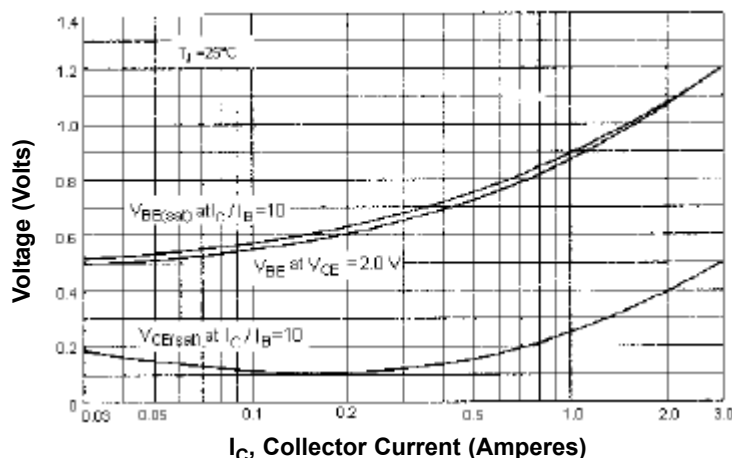
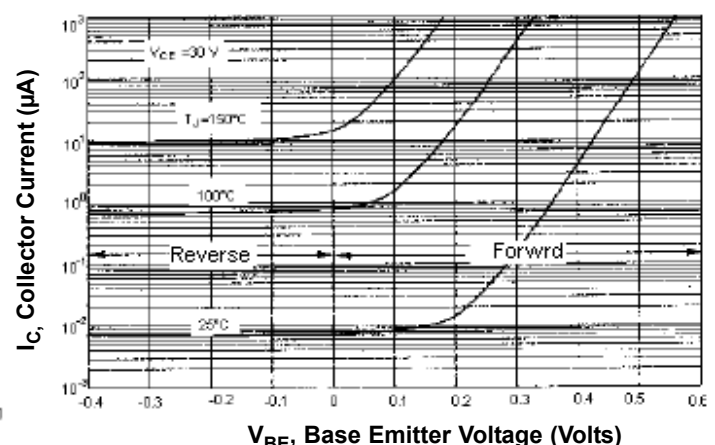


Figure - 10 Collector Cut-off Region



Part Number Table

Description	Type	Part Number
High Power Bipolar Transistor	NPN	TIP31A
High Power Bipolar Transistor		TIP31C
High Power Bipolar Transistor	PNP	TIP32A
High Power Bipolar Transistor		TIP32C

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